迪一電子®

E2AN THRU E2JN

2.0AMP SURFACE MOUNT GLASS SUPERFAST RECOVERY RECTIFIER

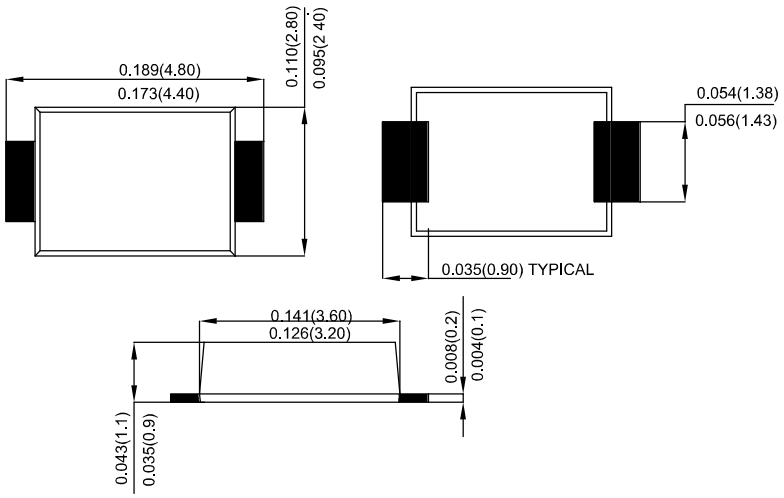
Features

- Low Power Loss, High Efficiency
- Ideally Suited for Automatic Assembly
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V- 0

Mechanical Data

- Case: Molded plastic SMAF
- Terminals: Plated leads solderable per MIL-STD-750,Method 2026 guaranteed
- Polarity: Color band dentes cathode end
- Mounting Position: Any
- Making: Type Number

SMAF



Dimiensions in inches and (milimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25℃ ambient temperature unless otherwise specified

Single phase,half wave,60Hz,resistive or inductive load

For capacitive load derate current by 20%

Type Number	SYMBOL	E2AN	E2BN	E2DN	E2GN	E2JN	Unit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	V
Average Rectified Output Current @T_L=100℃	I_O	2.0					A
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50					A
Forward Voltage @IF=2.0A	V_{FM}	0.95			1.25	1.7	V
Peak Reverse Current @T_A =25℃	I_R	5.0					uA
At Rated DC Blocking Voltage @T_A =100℃		150					
Maximum Reverse Recovery Time (Note 1)	Trr	35					ns
Typical Junction Capacitance (Note 2)	C_J	25					pF
Typical Thermal Resistance Junction to Ambient(Note 3)	$R_{\theta JA}$	34					℃/W
Operating Temperature Range	T_J	-55 to+150					℃
Storage Temperature Range	T_{STG}	-55 to +150					℃

Note: 1.Reverse Recovery Test Conditions:IF=0.5A,IR=1.0A,IRR=0.25A.

2. Measured at 1.0 MHz and Applied reverse Voltage of 4.0V D.C

3. 8.0MM²（.013mm Thick）Land Areas.

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FIG.1MAXIMUM AVERAGE FORWARD CURRENT DERATING

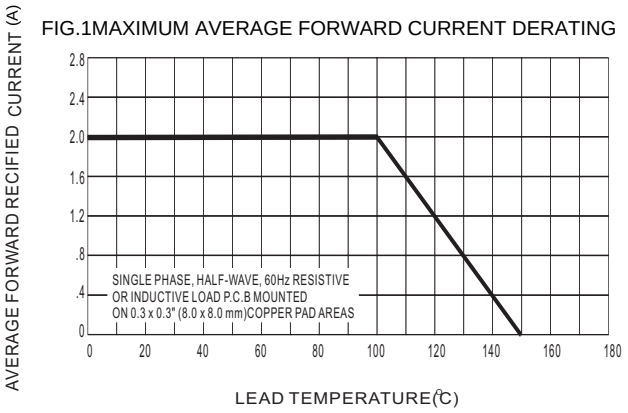

FIG.2TYPICAL FORWARD CHARACTERISTICS

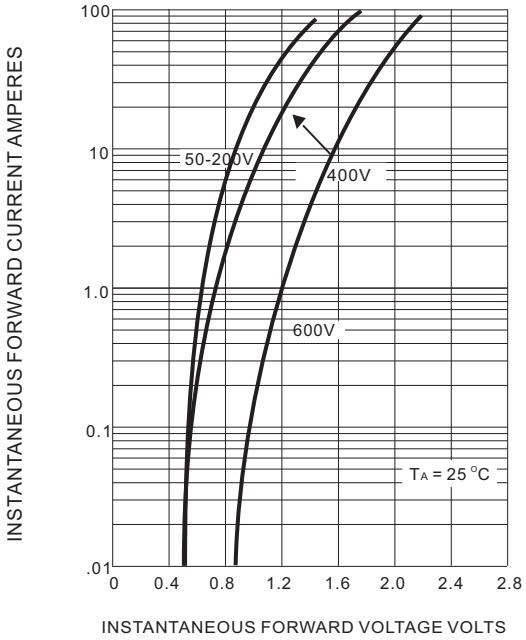

FIG.3MAXIMUM NON-REPEITIVE SURGE CURRENT

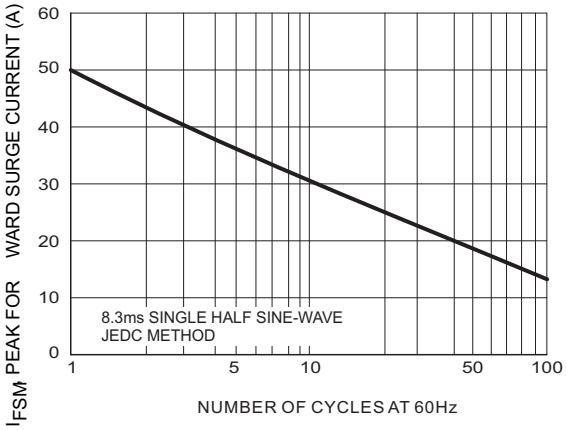

FIG.4TYPICAL JUNCTION CAPACITANCE

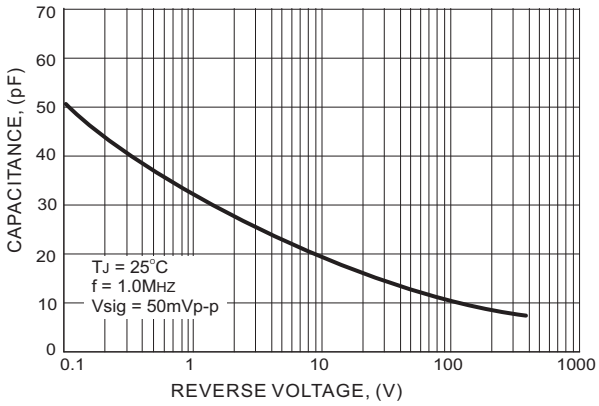

FIG.5TYPICAL REVERSE CHRACTERISTICS